# 1. General description

PNP low  $V_{CEsat}$  transistor and NPN Resistor- Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

## 2. Features and benefits

- Low V<sub>CEsat</sub> and resistor-equipped transistor in one package
- Low threshold voltage (<1 V) compared to MOSFET</li>
- · Low drive power required
- · Space-saving solution
- Reduction of component count

# 3. Applications

- · Supply line switches
- Battery charger switches
- · High-side switches for LEDs, drivers and backlights
- · Portable equipment

# 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
TR1; PNP lov	v V <sub>CEsat</sub> transistor						
$V_{CEO}$	collector-emitter voltage	open base		-	-	-40	V
I <sub>C</sub>	collector current			-	-	-500	mA
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -500 mA; $I_B$ = -50 mA; $T_{amb}$ = 25 °C	[1]	-	440	700	mΩ
TR2; NPN res	sistor-equipped transisto	r					
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	50	V
I <sub>O</sub>	output current			-	-	100	mA
R1	bias resistor 1 (input)		[2]	7	10	13	kΩ
R2/R1	bias resistor ratio		[2]	8.0	1	1.2	

- [1] Pulse test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$
- [2] See "Section 11: Test information" for resistor calculation and test conditions.



## 40 V 500 mA PNP/NPN loadswitch double transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1		C1 I2 GND2
2	B1	base TR1	П6 П5 П4	
3	O2	output (collector) TR2		R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2	H <sub>1</sub> H <sub>2</sub> H <sub>3</sub>	TR1
6	C1	collector TR1	TSSOP6 (SOT363)	E1 B1 O2 sym036

# 6. Ordering information

## **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PBLS4003Y		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	<u>SOT363</u>			

# 7. Marking

## Table 4. Marking codes

Type number	Marking code[1]
PBLS4003Y	S3%

[1] % = placeholder for manufacturing site code

## 40 V 500 mA PNP/NPN loadswitch double transistor

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
TR1; PNP Id	ow V <sub>CEsat</sub> transistor		,	<u> </u>		
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-40	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-40	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-500	mA
I <sub>CM</sub>	peak collector current	t <sub>p</sub> ≤ 1 ms; single pulse		-	-1	Α
I <sub>B</sub>	base current			-	-50	mA
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	200	mW
TR2; NPN r	esistor-equipped transistor			'	•	
V <sub>CBO</sub>	collector-base voltage	open emitter		-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	10	V
VI	input voltage	positive		-	40	V
		negative		-	-10	V
Io	output current			-	100	mA
I <sub>CM</sub>	peak collector current	t <sub>p</sub> ≤ 1 ms; single pulse		-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	200	mW
Per device	'			'	•	
P <sub>tot</sub>	total power dissipation			-	300	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.

## 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.

PBLS4003Y

## 40 V 500 mA PNP/NPN loadswitch double transistor

# 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
TR1; PNP I	ow V <sub>CEsat</sub> transistor						
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -40 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	-100	nA
	current	V <sub>CB</sub> = -40 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	-50	μA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; $I_{C}$ = -10 mA; $T_{amb}$ = 25 °C		200	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -100 mA; $T_{amb}$ = 25 °C	[1]	150	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -500 mA; $T_{amb}$ = 25 °C	[1]	40	-	-	
V <sub>CEsat</sub>	collector-emitter	$I_C$ = -10 mA; $I_B$ = -0.5 mA; $T_{amb}$ = 25 °C		-	-	-50	mV
	saturation voltage	$I_C$ = -100 mA; $I_B$ = -5 mA; $T_{amb}$ = 25 °C		-	-	-130	mV
		$I_C$ = -200 mA; $I_B$ = -10 mA; $T_{amb}$ = 25 °C		-	-	-200	mV
		$I_C$ = -500 mA; $I_B$ = -50 mA; $T_{amb}$ = 25 °C	[1]	-	-	-350	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance		[1]	-	440	700	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage		[1]	-	-	-1.2	V
$V_{BEon}$	base-emitter turn-on voltage	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -100 mA; T <sub>amb</sub> = 25 °C	[1]	-	-	-1.1	V
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C		-	-	10	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -100 mA; f = 100 MHz; $T_{amb}$ = 25 °C		100	300	-	MHz
TR2; NPN r	esistor-equipped transisto	· •			'		'
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	1	μΑ
	current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	400	μA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 5 mA; T <sub>amb</sub> = 25 °C		30	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	150	mV
V <sub>I(off)</sub>	off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA; T <sub>amb</sub> = 25 °C		-	1.1	0.8	V
V <sub>I(on)</sub>	on-state input voltage	V <sub>CE</sub> = 0.3 V; I <sub>C</sub> = 10 mA; T <sub>amb</sub> = 25 °C		2.5	1.8	-	V
R1	bias resistor 1 (input)		[2]	7	10	13	kΩ
R2/R1	bias resistor ratio		[2]	0.8	1	1.2	
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C		-	-	2.5	pF
		1				1	1

Pulse test:  $t_p \le 300~\mu s$ ;  $\delta \le 0.02$ See "Section 11: Test information" for resistor calculation and test conditions.

#### 40 V 500 mA PNP/NPN loadswitch double transistor

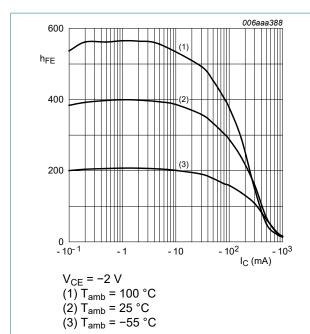


Fig. 1. TR1 (PNP): DC current gain as a function of collector current; typical values

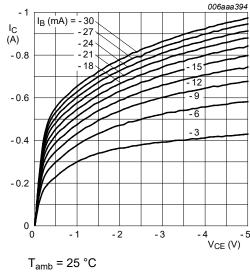


Fig. 2. TR1 (PNP): Collector current as a function of collector-emitter voltage; typical values

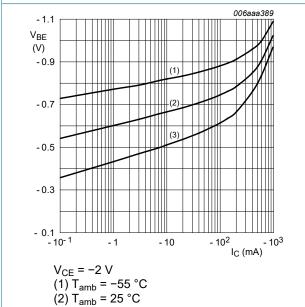
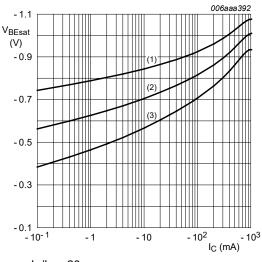


Fig. 3. TR1 (PNP): Base-emitter voltage as a function of collector current; typical values

(3) T<sub>amb</sub> = 100 °C



 $I_{\rm C}/I_{\rm B} = 20$ (1)  $T_{\rm amb} = -55~{\rm ^{\circ}C}$ (2)  $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3)  $T_{\rm amb} = 100~{\rm ^{\circ}C}$ 

Fig. 4. TR1 (PNP): Base-emitter saturation voltage as a function of collector current; typical values

#### 40 V 500 mA PNP/NPN loadswitch double transistor

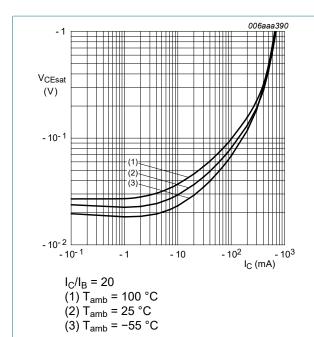
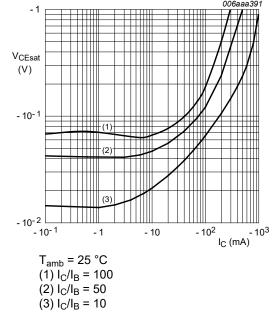
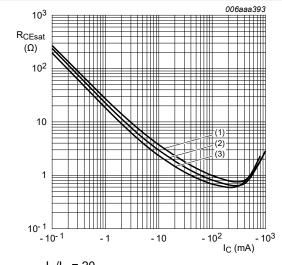


Fig. 5. TR1 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



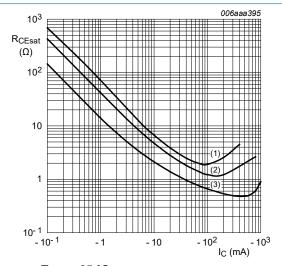
(3) I<sub>C</sub>/I<sub>B</sub> = 10

Fig. 6. TR1 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



 $I_C/I_B = 20$ (1)  $T_{amb} = 100 \,^{\circ}C$ (2)  $T_{amb} = 25 \,^{\circ}C$ (3)  $T_{amb} = -55 \,^{\circ}C$ 

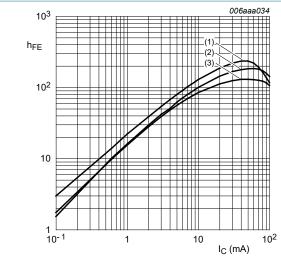
Fig. 7. TR1 (PNP): Collector-emitter saturation resistance as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}\text{C}$ (1)  $I_{C}/I_{B} = 100$ (2)  $I_{C}/I_{B} = 50$ (3)  $I_{C}/I_{B} = 10$ 

Fig. 8. TR1 (PNP): Collector-emitter saturation resistance as a function of collector current; typical values

#### 40 V 500 mA PNP/NPN loadswitch double transistor

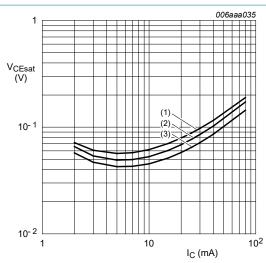


$$V_{CE} = 5 V$$

$$(1) T_{amb} = 150 ° ($$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

TR2 (NPN): DC current gain as a function of Fig. 9. collector current; typical values



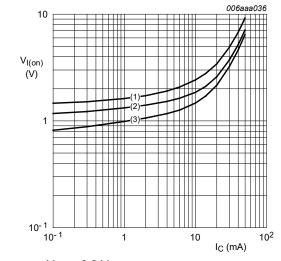
$$I_{\rm C}/I_{\rm B} = 20$$

$$I_{C}/I_{B} = 20$$
(1)  $T_{amb} = 100 \, ^{\circ}C$ 
(2)  $T_{amb} = 25 \, ^{\circ}C$ 
(3)  $T_{amb} = -40 \, ^{\circ}C$ 

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 10. TR2 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



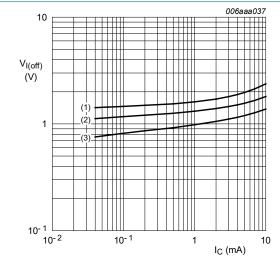
$$V_{CE}$$
 = 0.3  $V$ 

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = 100 °C$$

of collector current; typical values



$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

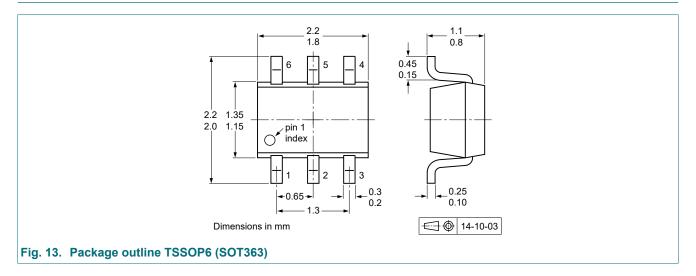
(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

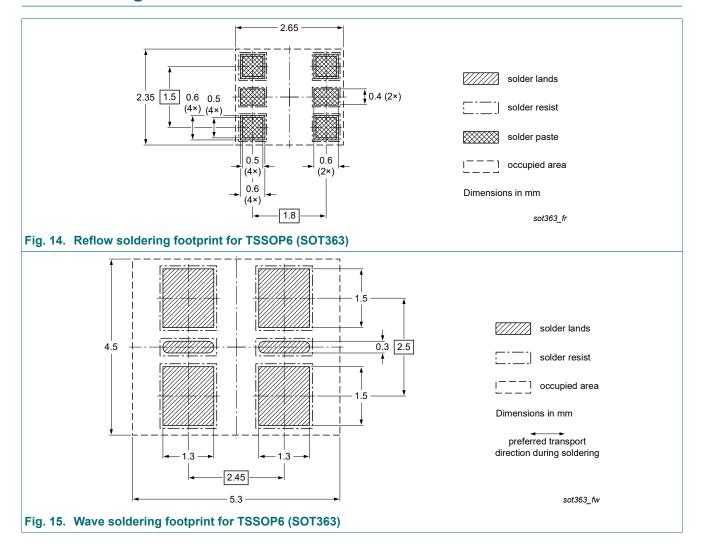
Fig. 11. TR2 (NPN): On-state input voltage as a function | Fig. 12. TR2 (NPN): Off-state input voltage as a function of collector current; typical values

## 40 V 500 mA PNP/NPN loadswitch double transistor

# 11. Package outline



# 12. Soldering



## 40 V 500 mA PNP/NPN loadswitch double transistor

# 13. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBLS4003Y v.4	20241008	Product data sheet	-	PBLS4003Y_PBLS400 3V_3
Modifications:	•	reduced to single type da to non automotive. Please		e product(s) with -Q.
PBLS4003Y_PBLS400 3V_3	20090213	Product data sheet	-	PBLS4003Y_PBLS400 3V_2
PBLS4003Y_PBLS400 3V_2	20050714	Product data sheet	-	PBLS4003Y_PBLS400 3V_1
PBLS4003Y_PBLS400 3V_1	20041206	Product data sheet	-	

## 14. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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## 40 V 500 mA PNP/NPN loadswitch double transistor

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